

FORM PTO-1449

MAR 26 2004

U.S. DEPARTMENT OF COMMERCE
PATENT AND TRADEMARK OFFICEATTY. DOCKET NO.
990559SÉRIAL NO.
09/320,271

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT

WATANABE et al.

FILING DATE

May 27, 1999

GROUP

2825

U.S. PATENT DOCUMENTS

EXAMINER INITIAL	DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
CL AA	5,024,723	06/18/91	Goesele, et al.	156	628	
	AB 5,616,513	04/01/97	Shepard	438	402	
	AC 5,674,784	10/07/97	Jang, et al.	437	195	
	AD 5,723,895	03/03/98	Takahashi	257	499	
	AE 5,830,773	11/03/98	Brennan, et al.	437	67	
	AF 5,581,101	12/3/96	Ning et al.	257	347	
	AG 4,962,052	10/09/90	Asayama, et al.	437	31	
	AH 5,930,624	07/27/99	Murata, et al.	438	253	
	AI 5,153,680	10/06/92	Naito, et al.	438	687	
	AJ 3,747,203	07/24/73	Shannon	438	629	
	AK 5,166,768	11/24/92	Ito	438	637	
	AL 4,676,867	06/30/87	Elkins, et al.	156	643	
	AM 4,775,550	10/04/88	Chu, et al.	427	38	
	AN 4,885,262	12/05/89	Ting, et al.	437	231	
	AO 4,983,546	01/08/91	Hyun, et al.	437	231	
	AP 5,003,062	03/26/91	Yen	437	231	
	AQ 5,106,787	04/21/92	Yen	437	231	
	AR 5,352,630	10/04/94	Kim, et al.	437	195	
	AS 5,549,786	08/27/96	Jones, et al.	156	662.1	
	AT 4,984,055	01/1991	Okumura, et al.	257	644	
	AU 5,270,259	12/1993	Ito, et al.	437	235	
	AV 5,468,684	11/1995	Yoshimori, et al.	437	228	
	AW 5,087,589	02/11/92	Chapman, et al.	437	195	
	AX 5,963,827	10/1999	Enomoto et al.	438	629	
	AY 5,341,026	08/23/94	Harada, et al.	257	764	
CL AZ	5,514,910	05/07/96	Koyama	257	768	

ATTY
990559SERIAL NO.
09/320,271

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT

WATANABE et al.

FILING DATE

May 27, 1999

GROUP
2825

U.S. PATENT DOCUMENTS (CONTINUED)

EXAMINER INITIAL		DOCUMENT NO.	DATE	NAME	CLASS	SUB-CLASS	FILING DATE
CL	BA	5,607,880	03/04/97	Suzuki	437	195	
	BB	5,702,568	12/30/97	Shin, et al.	156	644	
	BC	5,314,834	08/26/91	Mazure, et al.	438	595	
	BD	5,866,476	02/02/99	Choi, et al.	438	624	
	BE	5,084,412	01/28/92	Nakasaki	437	189	
	BF	5,479,054	12/26/95	Tottori	257	752	
	BG	5,753,975	05/19/98	Matsuno	257	751	
	BH	6,013,578	01/2000	Jun	438	687	
	BI	5,817,582	10/06/98	Maniar	438	782	
	BJ	5,569,618	10/29/96	Matsubara	437	52	
	BK	5,186,745	02/16/93	Maniar	106	287	
	BL	5,496,776	03/05/96	Chien, et al.	437	231	
	BM	5,855,962	01/05/99	Cote, et al.	427	376	
CL	BN						

FOREIGN PATENT DOCUMENTS

		DOCUMENT NO.	DATE	COUNTRY	TRANSLATION YES NO
CL	BO	02-235358	09/18/90	Japan	Abstract
	BP	JP 6-291202	10/18/94	Japan	Abstract
	BQ	JP 63 198359	8/17/88	Japan	Abstract
	BR	10-303295	11/13/98	Japan	Abstract
	BS	59-017243	01/28/84	Japan	Abstract
	BT	58-031519	02/24/83	Japan	Abstract
	BU	10-209147	08/07/98	Japan	Abstract
	BV	08-241891	09/17/96	Japan	Abstract
	BW	09-330982	12/22/97	Japan	Abstract
	BX	62-060242	03/16/87	Japan	Abstract
	BY	01-199456	08/10/89	Japan	Abstract
CL	BZ	03-101130	04/25/91	Japan	Abstract

ATTY
990559SERIAL NO.
09/329,271

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT

WATANABE et al.

FILING DATE

May 27, 1999

GROUP
2825

FOREIGN PATENT DOCUMENTS (CONTINUED)

		DOCUMENT NO.	DATE	COUNTRY	TRANSLATION Yes No
CL	CA	05-074963	03/26/93	Japan	Abstract
	CB	06-349950	12/22/94	Japan	Abstract
	CC	02-026055	01/29/90	Japan	Abstract
	CD	04-234149	08/21/92	Japan	Abstract
	CE	07-099195	04/11/95	Japan	Abstract
	CF	02-253643	10/12/90	Japan	Abstract
	CG	02-007451	01/11/90	Japan	Abstract
	CH	08-017770	01/19/96	Japan	Abstract
	CI	06-275229	09/30/94	Japan	Abstract
	CJ	05-198523	08/06/93	Japan	Abstract
	CK	04-317358	11/09/92	Japan	Abstract
	CL	08-064561	03/08/96	Japan	Abstract
	CM	01-307247	12/12/89	Japan	No
	CN	JP 56-125844	10/2/81	Japan	Abstract
	CO	02-101532	08/13/90	Japan	Yes
	CP	02-235358	09/18/90	Japan	Yes
	CQ	04-307934A	10/30/92	Japan	No
CL	CR	DE 42 18 495	12/10/92	Germany	No

OTHER REFERENCES (Including Author, Title, Date, Pertinent Pages, Etc.)

CL	CS	"Multilevel-Interconnection Technology for VLSI and ULSI," Silicon Processing for the VLSI Era - Volume II, (pp. 232-233).
	CT	"Lithography I: Optical Resist Material and Process Technology," (pp. 441).
	CU	1995 Proceedings 12th International VLSI Multilevel Interconnection Conference (VMIC Catalog No. 95ISMIC - 104), June 27-29, 1995.
	CV	Wang, et al., "A Study of Plasma Treatments on Siloxane SOB," IEEE VMIC Conference, June 7-8, 1994, pp. 101-107.
CL	CW	Chiang, et al., "Defects Study on Spin on Glass Planarization Technology," IEEE VMIC Conference, June 15-16, 1987, pp. 404-412.

ATTY
990559SERIAL NO.
09/320,271

LIST OF REFERENCES CITED BY APPLICANT

(Use several sheets if necessary)

APPLICANT
WATANABE et al.FILING DATE
May 27, 1999GROUP
2825

OTHER REFERENCES - CONTINUED (Including Author, Title, Date, Pertinent Pages, Etc.)

<i>Cl</i>	CX	Lai-Juh Chen, et al., "Fluorine-Implanted Treatment (FIT) SOG for the Non-Etchback Intermetal Dielectric," IEEE VMIC Conference, June 7-8, 1994, pp. 81-86.
	CY	Moriya, et al., "Modification Effects in Ion-Implanted SiO ₂ Spin-on-Glass," Journal of Electrochem. Soc., Vol. 140, No. 5, May 1993, pp. 1442-1450.
	CZ	Matsuura, et al., "An advance Interlayer Dielectric System with Partially Converted Organic SOG Using Plasma Treatment," IEEE VMIC Conference, June 8-9, 1993, pp. 113-115.
	DA	Ishida, et al., "Mechanism for AlSiCu Alloy Corrosion," Japanese Journal of Applied Physics, Vol. 31 (1992), pp. 2045-2048.
	DB	Doki, et al., "Moisture-Blocking Mechanism of ECR-Plasma," IEEE VMIC Conference, June 7-8, 1994, pp. 235-239.
	DC	Shimokawa, et al., "Suppression of MOSFET Hot Carrier Degradation by P-SiO Underlayer," The Institute of Electronics, Information and Communication Engineers, Technical Report of IEICE, SDM92-133 (1992-12), pp. 89-94.
<i>Cl</i>	DD	Murase, et al., "Dielectric Constant of Silicon Dioxide Deposited by Atmospheric-Pressure Chemical Vapor Deposition Using Tetraethylorthosilicate and Ozone," Japanese Journal of Applied Physics, Vol. 33, (1994), pp. 1385-1389.

EXAMINER <i>calvinkle</i>	DATE CONSIDERED <i>5. 9. 04</i>
*EXAMINER: Initial if reference considered, whether or not citation is in conformance with MPEP 609; Draw line through citation if not in conformance and not considered. Include copy of this form with next communication to applicant.	

OTHER DOCUMENTS

<u>CL</u>	AR	Wolf et al."Silicon Processing for the VLSI Era: Volume I - Process Technology," "Lattice Press, 1986 p. 441.
<u>CL</u>	AS	Office Action of Japanese Application No. 09-234456.
<u>CL</u>	AJ	OFFICE Action of JAPANESE Application No. 08-181593.
<u>CL</u>	AU	Office Action of Japanese Application No. 09-204942.
<u>CL</u>	AV	Office Action of Japanese Application No. 08-345587.
<u>CL</u>	AW	Office Action Of Japanese Application No. 09-012788.
<u>CL</u>	AX	Office Action of Japanese Application No. 07-227294..
	AY	
<i>Calvinkle</i>		Date Considered
		5. 09. 04

Related Copending Applications

<u>Application No.</u>	<u>Filing Date</u>	<u>Attorney Docket No.</u>	<u>Status</u>
08/921,250	8/29/97	970813	Pending
08/806,425	2/26/97	970150	5,892,269 (Issued)
09/228,148	1/11/99	970150A	Pending
09/160,044	09/25/98	981187	6,235,648 (Issued)
09/716,334	11/21/00	981187A	Pending
08/923,901	09/04/97	970952	6,288,438 (Issued)

calwanda

5/13/04